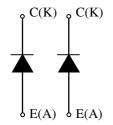
DM400E33

Preliminary Specification

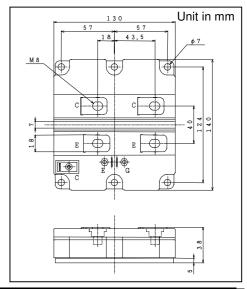
FEATURES

- * Low noise due to soft and fast recovery diodes.
- * High reliability, high durability diodes.
- * Isolated heat sink(terminal to base).

CIRCUIT DIAGRAM



OUTLINE DRAWING



ABSOLUTE MAXIMUM RATINGS (TC=25°C)

Item			Symbol	Unit	MDM400E33D
Repetitive Peak Reverse Voltage			V_{RRM}	V	3,300
Forward Current		DC	l _F	Α	400
		1ms	I _{FM}		800
Junction Temperature			Tj	°C	-40 ∼ +125
Storage Temperature			Tstg	°C	-40 ∼ +125
Isolation Test Voltage			V_{ISO}	V_{RMS}	6,000(AC 1 minute)
Screw Torque	Terminals (M8)		-	N·m	10 (1)
	Mounting (M6)		-	INIII	6 (2)

Notes: (1) Recommended Value 9±1N·m

(2) Recommended Value 5.5±0.5N·m

ELECTRICAL CHARECTERISTICS

Item	Symbol	Unit	Min.	Тур.	Max.	Test Conditions
Repetitive Reverse Current	I _{RRM}	mΑ	-	1.0	10.0	VAK=3,300V, Tj=125°C
Forward Voltage Drop	V_{F}	V	-	2.5	3.0	IF=400A, Tj=125°C at chip level
Reverse Recovery Time	trr	μs	-	0.4	0.7	V _{CC} =1,650V, Ic=400A, L=100nH
Reverse Recovery Loss	E _{rr(10%)}	J/P	-	0.4	0.7	Tj=125°C

PACKAGE CHARECTERISTICS

Item	Symbol	Unit	Min.	Тур.	Max.	Test Conditions
Terminal Resistance	RCE	$m\Omega$	-	0.4	-	Tc=25°C
Terminal Stray Inductance	Lsce	nΗ	-	35	-	
Partial Discharge Extinction Voltage	Vex	Vrms	2.5	-	-	f=50Hz, Q<10pC
Thermal Impedance	Rth(j-c)	K/W	ı	-	0.051	Junction to case
Comparative tracking index	CTI		-	600	-	
Contact Thermal Impedance	Rth(c-f)	K/W	-	0.008	-	Case to fin per module

^{*} For improvement, specifications are subject to change without notice.

^{*} For actual application, please confirm this spec sheet is the newest revision.

* Due to technical requirement, this product may contain restricted material for some application. Please contact our representatives.

HITACHI POWER SEMICONDUCTORS

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